

AMENDMENTS TO THE CLAIMS

1. (Original) A light device comprising:

a GaN-based layer;

a high concentration GaN-based layer formed on the GaN-based layer;

a first metal-Ga compound layer formed on the high concentration GaN-based layer;

a first metal layer formed on the first metal-Ga compound layer;

a third metal-Al compound layer formed on the first metal layer; and

a conductive oxidation preventive layer formed on the third metal-Al compound layer.

2-3. (Cancelled)

4. (Currently Amended) The light device ~~of any one according to claims 1 to 3~~claim 1, wherein the GaN-based layer is P-type or N-type.

5. (Currently Amended) The light device ~~of any one according to claims 1 to 3~~claim 1, wherein the first metal layer is of one selected from the group consisting of Cr, V and W.

6. (Currently Amended) The light device ~~of any one according to claims 1 to 3~~claim 1, wherein the first metal layer is of a metal or compound having a high reactivity with Ga and N.

7. (Currently Amended) The light device ~~of any one according to claims 1 to 3~~claim 1, wherein the third metal is of one selected from the group consisting of Ni, Pt and Pd.

8. (Currently Amended) The light device ~~of any one~~ according to ~~claims 1 to 3~~claim 1, wherein the third metal is of a metal or compound having a high reactivity with Al.

9. (Currently Amended) The light device ~~of any one~~ according to ~~claims 1 to 3~~claim 1, wherein the third metal is of a metal or a compound not having a reactivity with the material forming the conductive oxidation preventive layer.

10. (Currently Amended) The light device ~~of any one~~ according to ~~claims 1 to 3~~claim 1, wherein the conductive oxidation preventive layer is of Au, or is of a multi-metal or compound of two or more kinds containing Au.

11-52. (Cancelled)

53. (Currently Amended) The light device ~~of any one~~ according to ~~claims 1 to 3~~claim 1, wherein the light device comprises an NP-type light emitting device or an NPN-type light emitting device.

54. (Currently Amended) The light device ~~of any one~~ according to ~~claims 1 to 3~~claim 1, wherein the first metal layer is of one selected from the group consisting of Cr, V and W, and the third metal is of one selected from the group consisting of Ni, Pt and Pd.

55. (New) The light device according to claim 1, comprising a transparent electrode layer formed between the high concentration GaN-based layer and the first metal-Ga compound layer.

56. (New) The light device according to claim 55, wherein the GaN-based layer is P-type or N-type.

57. (New) The light device according to claim 55, wherein the first metal layer is of one selected from the group consisting of Cr, V and W, and the third metal is of one selected from the group consisting of Ni, Pt and Pd.